crystal orientation of an orientation of the cutting plane is integrally grown in the polycrystalline β-SiC plate in conformity with the single crystal α-SiC substrate.

The method of growing single crystal SiC according to a second aspect of the invention is characterized in that, under a state where (2 2 0) Miller index plane of a--

**Please replace the last paragraph on page 5 with the following:**

--In the thus configured first and second aspects of the invention, a state where the crystal growing conditions in the interface plane are substantially uniformalized, and micropipes of the single crystal α-SiC substrate are not transferred or converted to distortion is obtained by superimposing the planes in which arrangements of Si atoms and C atoms are identical, i.e., the cutting plane along the (1 1 $\bar{2}$ 0) Miller index plane $\pm$ 10° of the single crystal α-SiC substrate, and the (2 2 0) Miller index plane of the polycrystalline β-SiC plate, and heat treatment is then conducted in an inert gas atmosphere. As a result, solid phase growth in which the whole region of the interface plane of the polycrystalline β-SiC plate is converted substantially simultaneously and rapidly to α-SiC can be performed. Therefore, it is possible to grow single crystal which is free not only micropipes but also from distortion and residual grain boundaries due to uneven crystal growth rates, so that single crystal SiC of--

**Please replace the last paragraph on page 6 with the following:**

--In the method of growing single crystal SiC according to the second aspect of the invention, each of at least one cutting plane of the single crystal α-SiC substrate, and at least one (2 2 0) Miller index plane of the polycrystalline β-SiC plate may be processed into a smooth mirror face of 10 angstroms RMS or less. According to this configuration, the planes can be closely contacted with each other without leaving a gap therebetween. Therefore, single crystal